

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Errors
1	BRS	6	metal with gate near (dielectric or oxide or insulat\$) and oxide near mask with nitride near mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 23:45		0
2	BRS	5	metal with gate near (dielectric or oxide or insulat\$) and oxide with mask with nitride with mask with (pattern\$ or etch\$) and (ald or atomic near layer near deposit\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 23:49		0
3	BRS	32	metal with gate near (dielectric or oxide or insulat\$) and hard near mask with (pattern\$ or etch\$) and (ald or atomic near layer near deposit\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 00:02		0

	Typ e	Hi ts	Search Text	DBs	Time Stamp	C o m m e n t s	E r r o r D i f f e r e n c e s	E r r o r s
4	BRS	2	metal with gate near (dielectric or oxide or insulat\$) and hard near mask with oxide with nitride with (pattern\$ or etch\$) and (ald or atomic near layer near deposit\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 00:03			0
5	BRS	11	metal with gate near (dielectric or oxide or insulat\$) and mask with oxide same mask with nitride same (pattern\$ or etch\$) and (ald or atomic near layer near deposit\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 00:05			0
6	BRS	8	metal with gate near (dielectric or oxide or insulat\$) and mask with oxide same mask with nitride same (pattern\$ or etch\$) and (ald or atomic near layer near deposit\$) and anneal\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 00:06			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Corrections	Errors
7	BRS	1	metal with gate near (dielectric or oxide or insulat\$) and mask with oxide same mask with nitride same (pattern\$ or etch\$) and (ald or atomic near layer near deposit\$) and (anneal\$ or curing or cure\$ or densif\$) with	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 00:07			0
8	BRS	4	metal near gate and (metal or gate) with oxide with mask and oxide near mask with nitride near mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 16:08			0
9	BRS	4	metal near gate and oxide near mask with nitride near mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 16:09			0
10	BRS	62	metal near gate and oxide with nitride near mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 16:11			0
11	BRS	27	metal near gate and oxide near mask and nitride near mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 16:28			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Corrections	Errors
12	BRS	12	metal with gate and gate with stack\$5 and oxide with (ald or atomic near layer near deposit\$) and nitride with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 16:52			0
13	BRS	2	metal\$9 with gate and gate with stack\$5 and oxide with nitride with mask with (etch\$ or pattern\$) and (ald or atomic near layer near deposit\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 16:43			0
14	BRS	1	metal\$9 with gate and gate with stack\$5 and oxide near mask with nitride near mask with (etch\$ or pattern\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 16:46			0
15	BRS	10	metal\$9 with gate and oxide near mask with nitride near mask with (etch\$ or pattern\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 16:47			0
16	BRS	31	4149307.URPN.	USPAT	2004/09/01 16:50			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Errors
17	BRS	45	metal with gate with (etch\$ or pattern\$) and oxide with mask with nitride near mask with (etch\$ or pattern\$) and (ald or atomic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 16:58		0
18	BRS	32	metal with gate with (etch\$ or pattern\$) and oxide near mask with nitride with mask with (etch\$ or pattern\$) and (ald or atomic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 21:10		0
19	BRS	1	dual near mask with oxide with nitride with (etch\$ or pattern\$) and oxide near mask with (ald or atomic layer deposit\$) and (etch\$ or pattern\$) with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 22:09		0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
20	BRS	1	dual near mask with oxide with nitride with (etch\$ or pattern\$) and oxide near mask with (ald or atomic layer deposit\$) and metal\$9 with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 22:10			0
21	BRS	0	dual near mask with oxide with nitride with (etch\$ or pattern\$) and (ald or atomic near layer near deposit\$) and metal\$9 with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 22:12			0
22	BRS	0	dual near mask and oxide with nitride with (etch\$ or pattern\$) and (ald or atomic near layer near deposit\$) and metal\$9 with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 22:13			0
23	BRS	7	mask with oxide with nitride with (etch\$ or pattern\$) and (ald or atomic near layer near deposit\$) and metal\$9 with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 22:22			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
24	BRS	100	(oxide or oxy\$9) with nitride with (etch\$ or pattern\$) and (ald or atomic near layer near deposit\$) and metal\$9 with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 22:58			0
25	BRS	15	(oxide or oxy\$9) with nitride with (etch\$ or pattern\$) with mask and (ald or atomic near layer near deposit\$) and metal\$9 with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 22:26			0
26	BRS	28	(oxide or oxy\$9) with nitride with (etch\$ or pattern\$) and (ald or atomic near layer near deposit\$) and metal\$9 near gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 22:31			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
27	BRS	28	(oxide or oxy\$9) with nitride with (etch\$ or pattern\$) and (ald or atomic near layer near deposit\$) and metal\$9 with gate and gate near stack\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 22:59			0